

Title (en)
SEMICONDUCTOR ARRANGEMENT WITH NON-VOLATILE MEMORIES

Title (de)
HALBLEITERANORDNUNG MIT NICHTFLÜCHTIGEN SPEICHERN

Title (fr)
DISPOSITIF A SEMI-CONDUCTEURS ORGANIQUE COMPRENANT DES MEMOIRES NON VOLATILES

Publication
EP 1702369 A1 20060920 (DE)

Application
EP 04802810 A 20041124

Priority
• DE 2004002601 W 20041124
• DE 10355561 A 20031128

Abstract (en)
[origin: WO2005053027A1] The invention relates to a semiconductor arrangement comprising at least one non-volatile memory cell that is provided with a first electrode which consists of at least two layers. Said semiconductor arrangement further comprises an organic material that forms a bond with the layer of the first electrode, which is in direct contact therewith. The invention also relates to a method for producing said non-volatile memory cell, a semiconductor arrangement comprising a plurality of inventive memory cells, and a method for the production thereof.

IPC 8 full level
H01L 51/00 (2006.01); **C09D 5/24** (2006.01); **C09D 5/25** (2006.01); **G11C 13/02** (2006.01); **H01L 27/24** (2006.01); **H01L 27/28** (2006.01); **H01L 51/05** (2006.01); **H01L 51/30** (2006.01)

CPC (source: EP US)
B82Y 10/00 (2013.01 - EP US); **G11C 13/0014** (2013.01 - EP US); **G11C 13/0016** (2013.01 - EP US); **H10K 10/701** (2023.02 - EP US); **H10K 19/00** (2023.02 - US); **H10K 19/80** (2023.02 - EP); **H10K 85/113** (2023.02 - EP US); **H10K 85/611** (2023.02 - EP US); **H10K 85/649** (2023.02 - EP US)

Designated contracting state (EPC)
DE FR GB

DOCDB simple family (publication)
WO 2005053027 A1 20050609; DE 10355561 A1 20050630; EP 1702369 A1 20060920; US 2007194301 A1 20070823

DOCDB simple family (application)
DE 2004002601 W 20041124; DE 10355561 A 20031128; EP 04802810 A 20041124; US 58088104 A 20041124